

0039-7684-2SRD DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

HISAKO AOYAMA ET AL.

SERIAL NO: 09/558,053

FILED: APRIL 26, 2000

FOR: SEMICONDUCTOR DEVICE
AND PROCESS OF FABRICATING
THE SAME

: GROUP ART UNIT: 2823

: EXAMINER: EATON, K

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office Action dated October 24, 2000, please amend the above-identified application as follows:

IN THE CLAIMS

✓ Please amend the claim 28 as follows:

--28. (Amended) A process of fabricating a semiconductor device comprising the steps of:

forming a first insulating film on a semiconductor substrate;

forming a second insulating film on said first insulating film, said second insulating film being made of a material different from that of the first insulating film and having a thickness smaller than that of the first insulating film;

forming a third insulating film on said second insulating film, said third insulating being made of a material different from that of the second insulating film and having a

7/C
Shirasa
1-30-01



RECEIVED
JAN 26 2001
TECHNOLOGY CENTER 2800

C!